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April 1st, 2010 Renesas Electronics Corporation

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MOS FIELD EFFECT TRANSISTOR

2SK3353

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK3353 is N-channel MOS Field Effect Transistor designed for high current switching applications.

FEATURES

• Super low on-state resistance:

 $R_{DS(on)1} = 9.5 \, m\Omega \, MAX. \, (V_{GS} = 10 \, V, \, I_{D} = 41 \, A)$ $R_{DS(on)2} = 14 \, m\Omega \, MAX. \, (V_{GS} = 4 \, V, \, I_{D} = 41 \, A)$

- Low Ciss: Ciss = 4650 pF TYP.
- Built-in gate protection diode

ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK3353	TO-220AB
2SK3353-S	TO-262
2SK3353-ZJ	TO-263
2SK3353-Z	TO-220SMD ^{Note}

Note TO-220SMD package is produced only in Japan

(TO-220AB)

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vss = 0 V)	Voss	60	V
Gate to Source Voltage (Vps = 0 V)	Vgss	±20	V
Drain Current (DC) (Tc = 25°C)	I _{D(DC)}	±82	Α
Drain Current (pulse) Note1	D(pulse)	±328	Α
Total Power Dissipation (Tc = 25°C)	P⊤	95	W
Total Power Dissipation (T _A = 25°C)	P⊤	1.5	W
Channel Temperature	T_ch	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C
Single Avalanche Current Note2	las	45	Α
Single Avalanche Energy Note2	Eas	202	mJ

Notes 1. PW \leq 10 μ s, Duty cycle \leq 1%

2. Starting T_{ch} = 25°C, V_{DD} = 30 V, R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V



(TO-262)



(TO-263, TO-220SMD)



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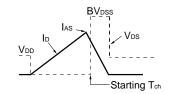


ELECTRICAL CHARACTERISTICS (TA = 25°C)

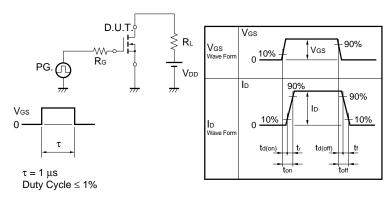
Characteristics	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 60 V, V _{GS} = 0 V			10	μА
Gate Leakage Current	lgss	Vgs = ±20 V, Vps = 0 V			±10	μΑ
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.5	2.0	2.5	V
Forward Transfer Admittance	Yfs	V _{DS} = 10 V, I _D = 41 A	30	50		S
Drain to Source On-state Resistance	RDS(on)1	VGS = 10 V, ID = 41 A		7.5	9.5	$m\Omega$
	RDS(on)2	Vgs = 4V, ID = 41 A		10.5	14	mΩ
Input Capacitance	Ciss	Vps = 10 V		4650		pF
Output Capacitance	Coss	V _G S = 0 V		780		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		380		pF
Turn-on Delay Time	td(on)	V _{DD} = 30 V, I _D = 41 A		100		ns
Rise Time	tr	V _{GS} = 10 V		1550		ns
Turn-off Delay Time	td(off)	$R_G = 10 \Omega$		280		ns
Fall Time	tf			420		ns
Total Gate Charge	Q _G	V _{DD} = 48 V		90		nC
Gate to Source Charge	Qgs	V _{GS} = 10 V		14		nC
Gate to Drain Charge	Q _{GD}	ID = 82 A		24		nC
Body Diode Forward Voltage	VF(S-D)	IF = 82 A, VGS = 0 V		1.0		V
Reverse Recovery Time	trr	IF = 82 A, VGS = 0 V		60		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		110		nC

TEST CIRCUIT 1 AVALANCHE CAPABILITY

$\begin{array}{c|c} \text{D.U.T.} \\ \text{Rg} = 25 \ \Omega \\ \text{Vgs} = 20 \rightarrow 0 \ V \end{array} \begin{array}{c} \text{D.U.T.} \\ \text{Rg} \\ \text{S} 50 \ \Omega \\ \text{M} \end{array} \begin{array}{c} \text{Vob} \\ \text{M} \end{array}$



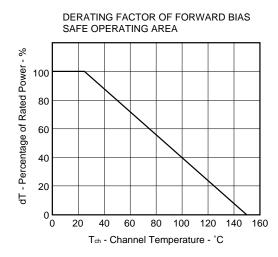
TEST CIRCUIT 2 SWITCHING TIME

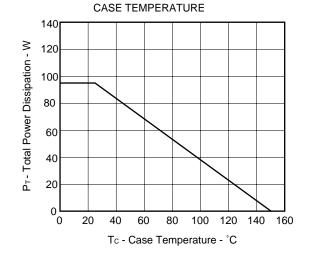


TEST CIRCUIT 3 GATE CHARGE

TYPICAL CHARACTERISTICS (TA = 25°C)

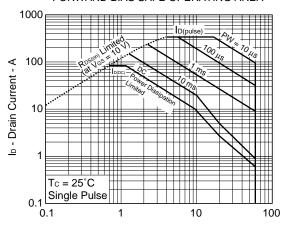
NEC



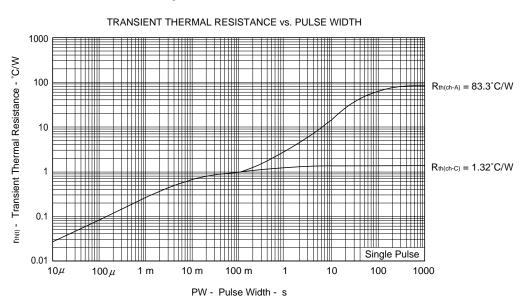


TOTAL POWER DISSIPATION vs.

FORWARD BIAS SAFE OPERATING AREA

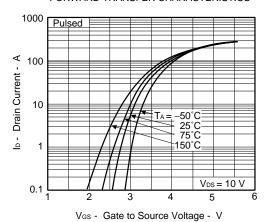


V_{DS} - Drain to Source Voltage - V

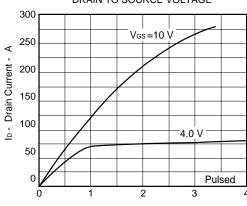


3

FORWARD TRANSFER CHARACTERISTICS

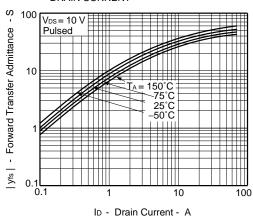


DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE

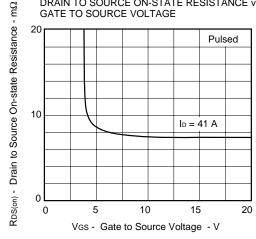


V_{DS} - Drain to Source Voltage - V

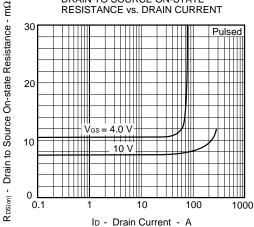
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



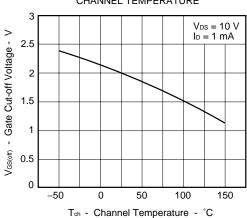
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



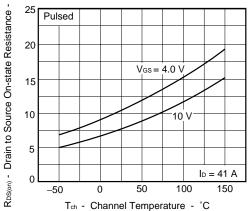
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



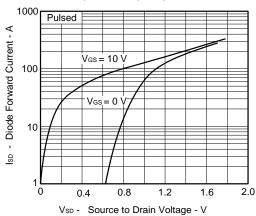


ДM

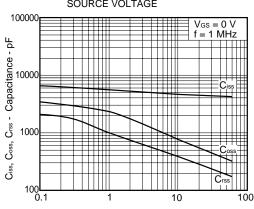




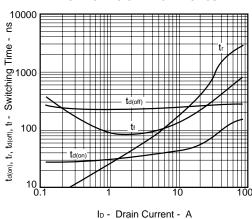
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



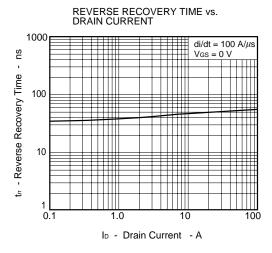
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



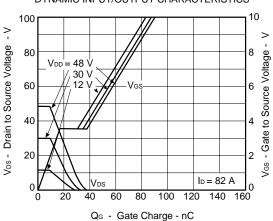
SWITCHING CHARACTERISTICS



V_{DS} - Drain to Source Voltage - V

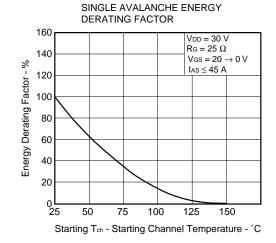


DYNAMIC INPUT/OUTPUT CHARACTERISTICS



5

SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD 1000 V: tuesday 100 IAs = 45AVideo = 30VRG = 25Ω Vise = $20 \rightarrow 0V$



L - Inductive Load - H

1 m

10 m

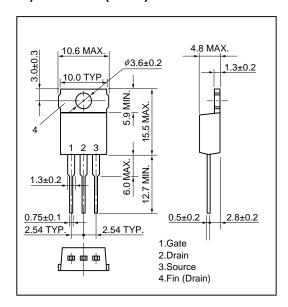
100 μ

10*μ*

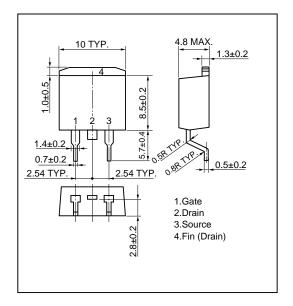


★ PACKAGE DRAWINGS (Unit: mm)

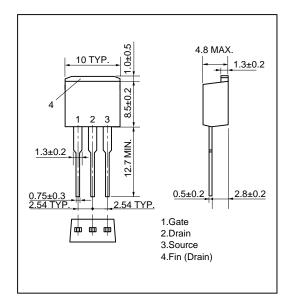
1) TO-220AB(MP-25)



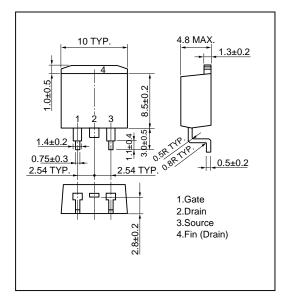
3) TO-263 (MP-25ZJ)



2) TO-262(MP-25 Fin Cut)

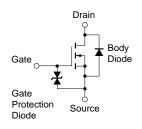


4) TO-220SMD (MP-25Z)^{Note}



Note This package is produced only in Japan.

EQUIVALENT CIRCUIT



Remark

The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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